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Stocking Distributor

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[Vishay/Siliconix](#)
[SI1431DH-T1-E3](#)

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Si1431DH
 Vishay Siliconix

P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
- 30	0.200 at V _{GS} = - 10 V	- 2.0
	0.355 at V _{GS} = - 4.5 V	- 1.6

FEATURES

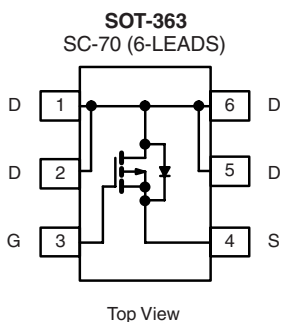
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



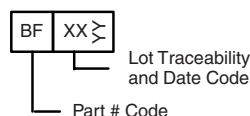
RoHS
 COMPLIANT
 HALOGEN
FREE
 Available

APPLICATIONS

- Load Switch
 - Notebook PC
 - Servers



Marking Code



Ordering Information: Si1431DH-T1-E3 (Lead (Pb)-free)
 Si1431DH-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	- 30		V	
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	- 2.0	- 1.7	A
		T _A = 85 °C	- 1.5	- 1.2	
Pulsed Drain Current	I _{DM}	- 8			
Continuous Diode Current (Diode Conduction) ^a	I _S	- 1.2	- 0.8		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	1.45	0.95	W
		T _A = 85 °C	0.75	0.5	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 5 s	65	85	°C/W
		Steady State	105	130	
Maximum Junction-to-Foot (Drain)	R _{thJF}	40	50		

Note:

a. Surface mounted on 1" x 1" FR4 board.

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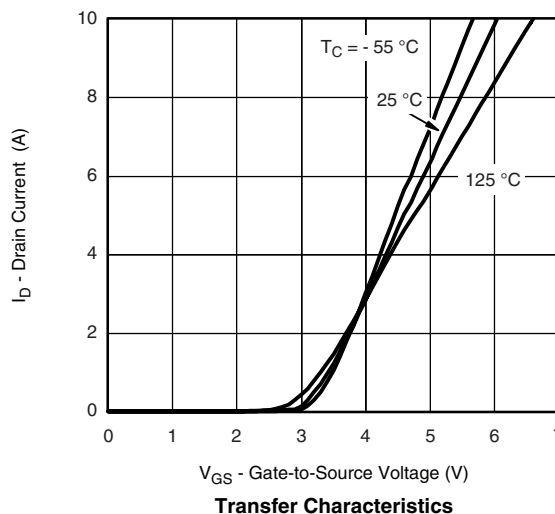
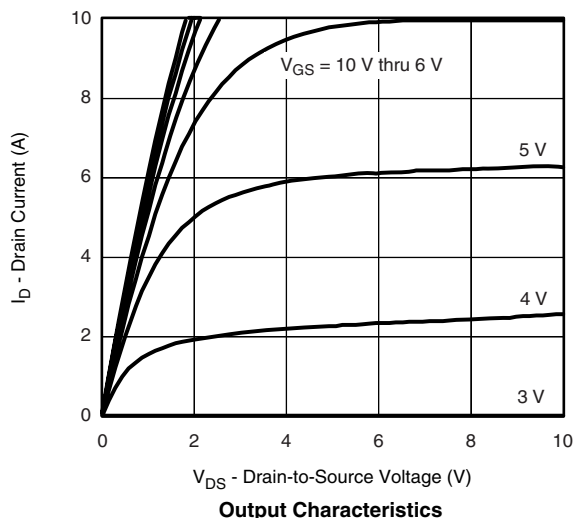
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -100\text{ }\mu\text{A}$	-1		-3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	-4			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -2.0\text{ A}$		0.160	0.200	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -1.6\text{ A}$		0.285	0.355	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -2.0\text{ A}$		2		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.2\text{ A}, V_{GS} = 0\text{ V}$		-0.85	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -2.0\text{ A}$		2.4	4	nC
Gate-Source Charge	Q_{gs}			0.8		
Gate-Drain Charge	Q_{gd}			1.3		
Gate Resistance	R_g	$f = 1.0\text{ MHz}$		9		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 6\text{ }\Omega$		55	80	ns
Rise Time	t_r			40	60	
Turn-Off Delay Time	$t_{d(off)}$			10	20	
Fall Time	t_f			10	20	

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

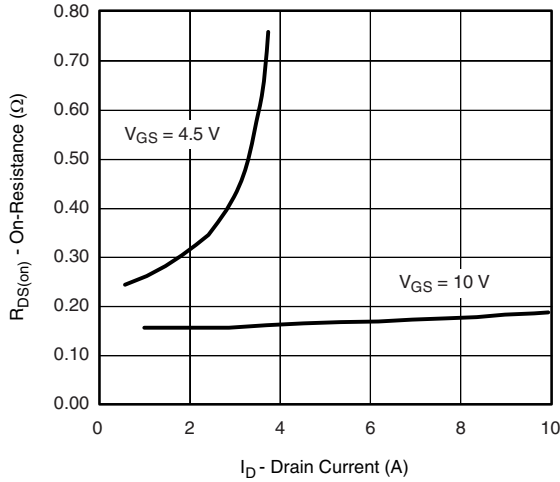
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



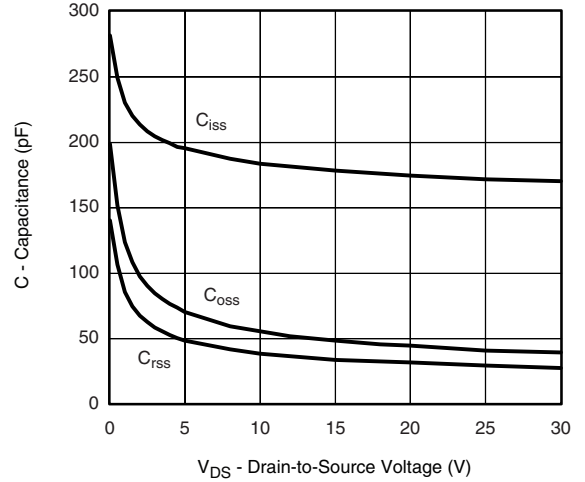


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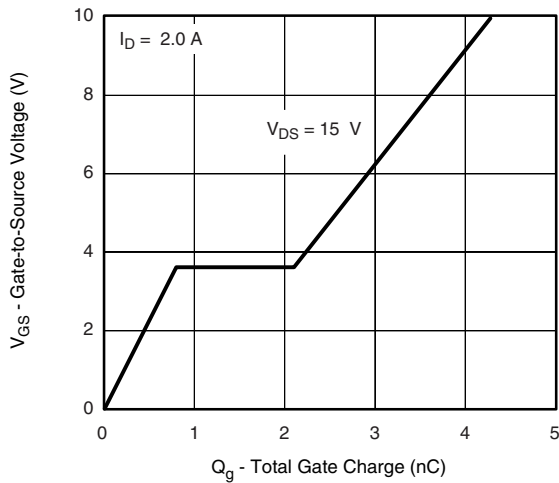
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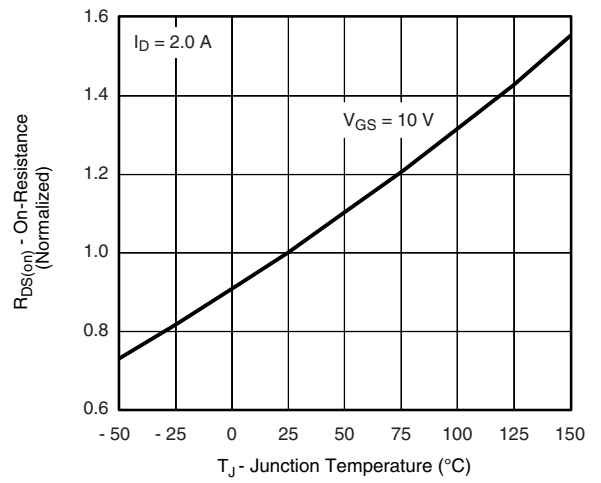
On-Resistance vs. Drain Current



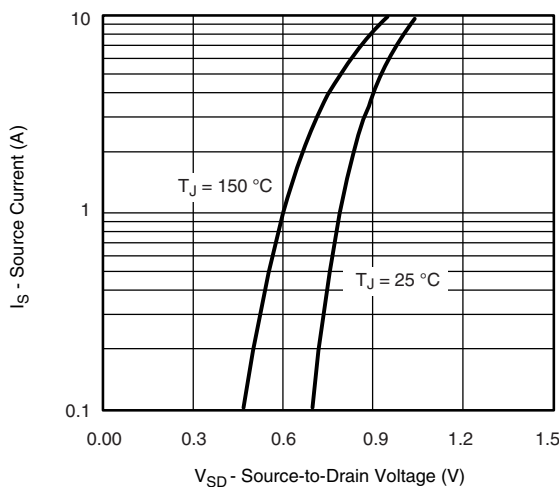
Capacitance



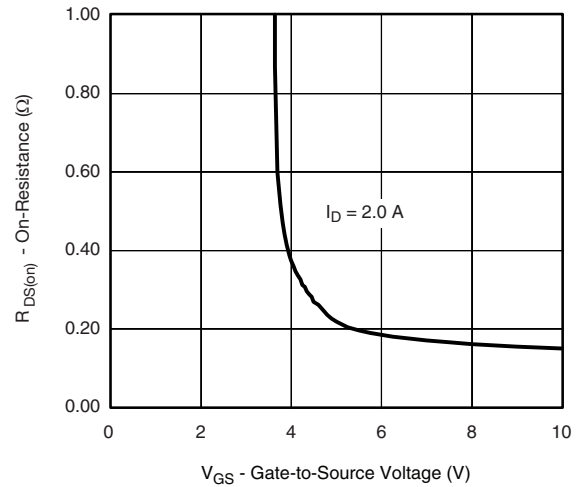
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



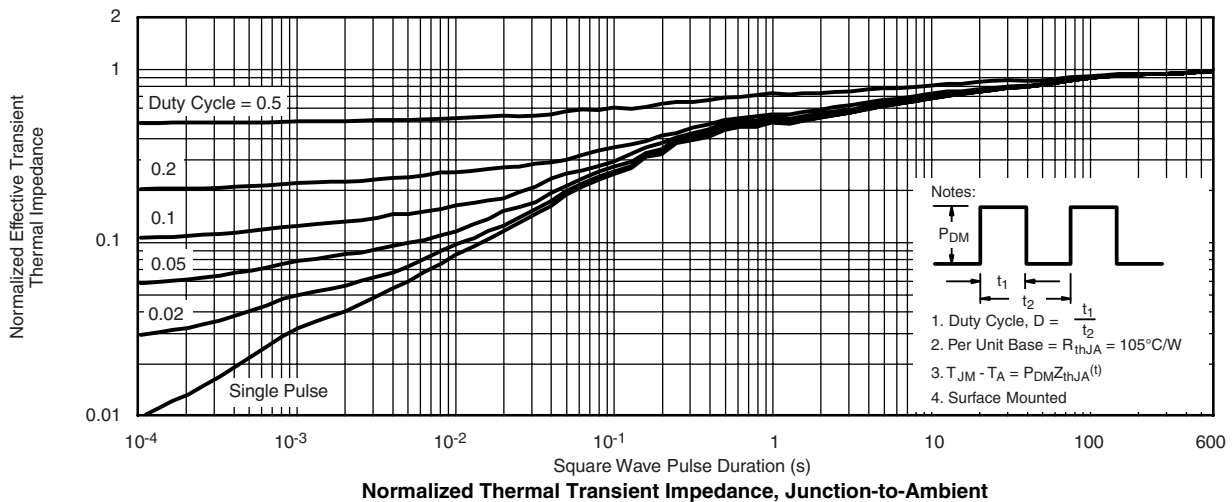
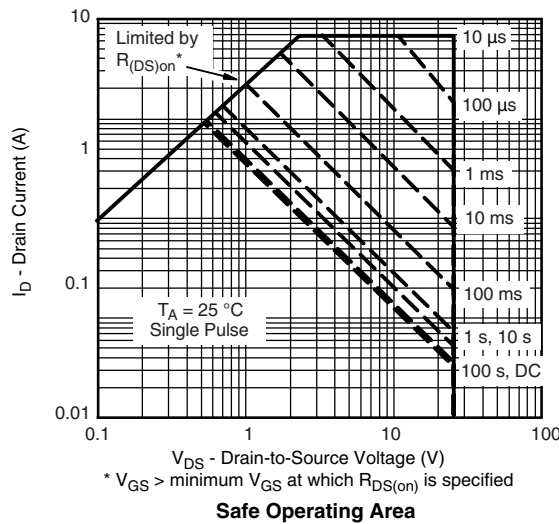
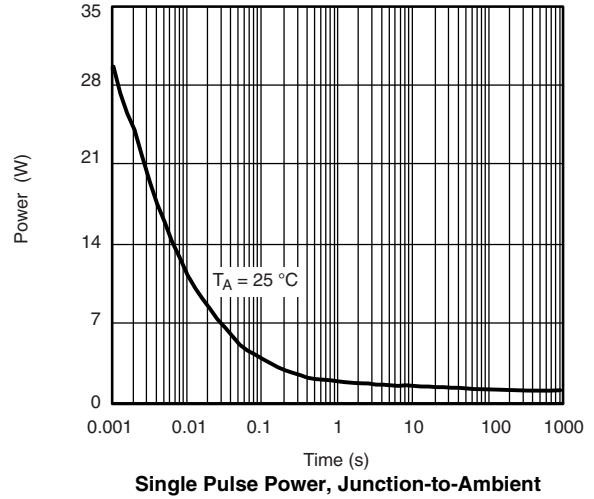
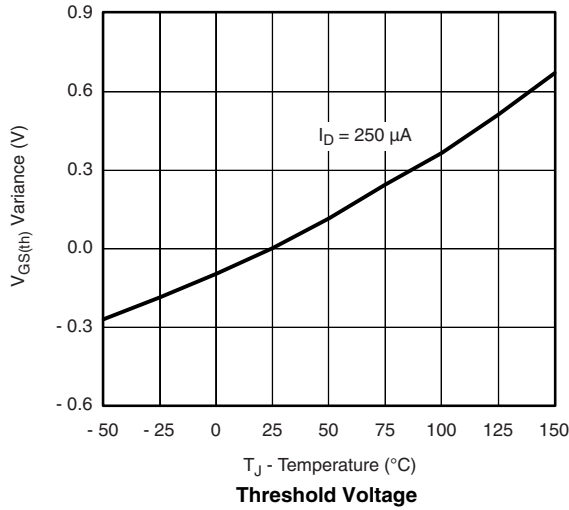
On-Resistance vs. Gate-to-Source Voltage

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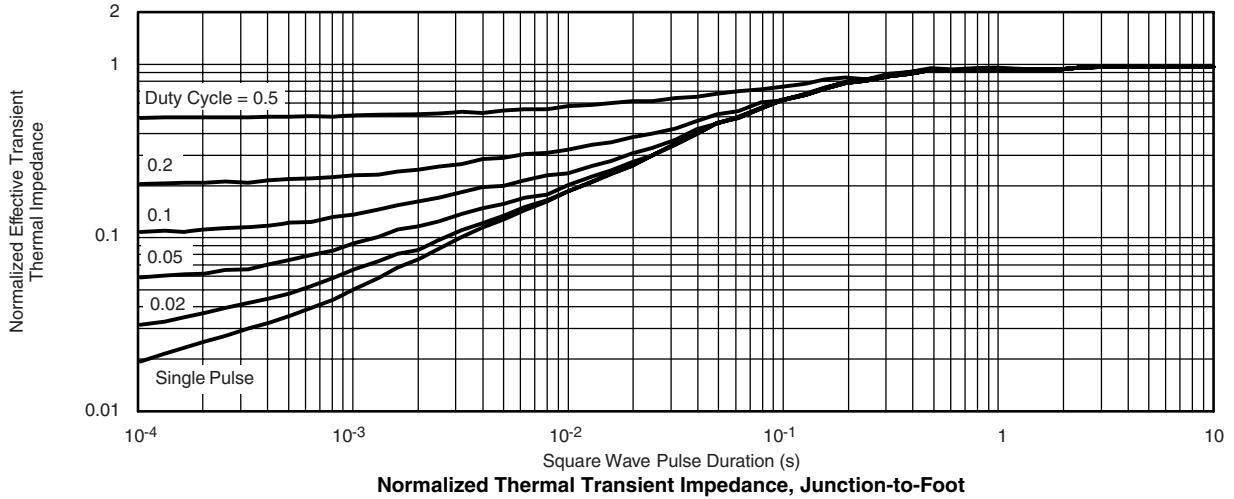
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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